Infineon Technologies - XMC1100T016F0016ABXUMA1 Datasheet

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, I²S, POR, PWM, WDT
Number of I/O	11
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 6x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	16-TSSOP (0.173", 4.40mm Width)
Supplier Device Package	PG-TSSOP-16-8
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xmc1100t016f0016abxuma1

About this Document

This Data Sheet is addressed to embedded hardware and software developers. It provides the reader with detailed descriptions about the ordering designations, available features, electrical and physical characteristics of the XMC1100 series devices.

The document describes the characteristics of a superset of the XMC1100 series devices. For simplicity, the various device types are referred to by the collective term XMC1100 throughout this document.

XMC™1000 Family User Documentation

The set of user documentation includes:

- **Reference Manual**
  – decribes the functionality of the superset of devices.
- **Data Sheets**
  – list the complete ordering designations, available features and electrical characteristics of derivative devices.
- **Errata Sheets**
  – list deviations from the specifications given in the related Reference Manual or Data Sheets. Errata Sheets are provided for the superset of devices.

Attention: Please consult all parts of the documentation set to attain consolidated knowledge about your device.

Application related guidance is provided by **Users Guides** and **Application Notes**.

Please refer to **http://www.infineon.com/xmc1000** to get access to the latest versions of those documents.

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Table 4 XMC1100 Chip Identification Number (cont'd)

Derivative	Value	Marking
XMC1100-Q040F0032	00011042 01CF00FF 00001F37 00000000 00000C00 00001000 00009000 201ED083$_H$	AB
XMC1100-Q040F0064	00011042 01CF00FF 00001F37 00000000 00000C00 00001000 00011000 201ED083$_H$	AB

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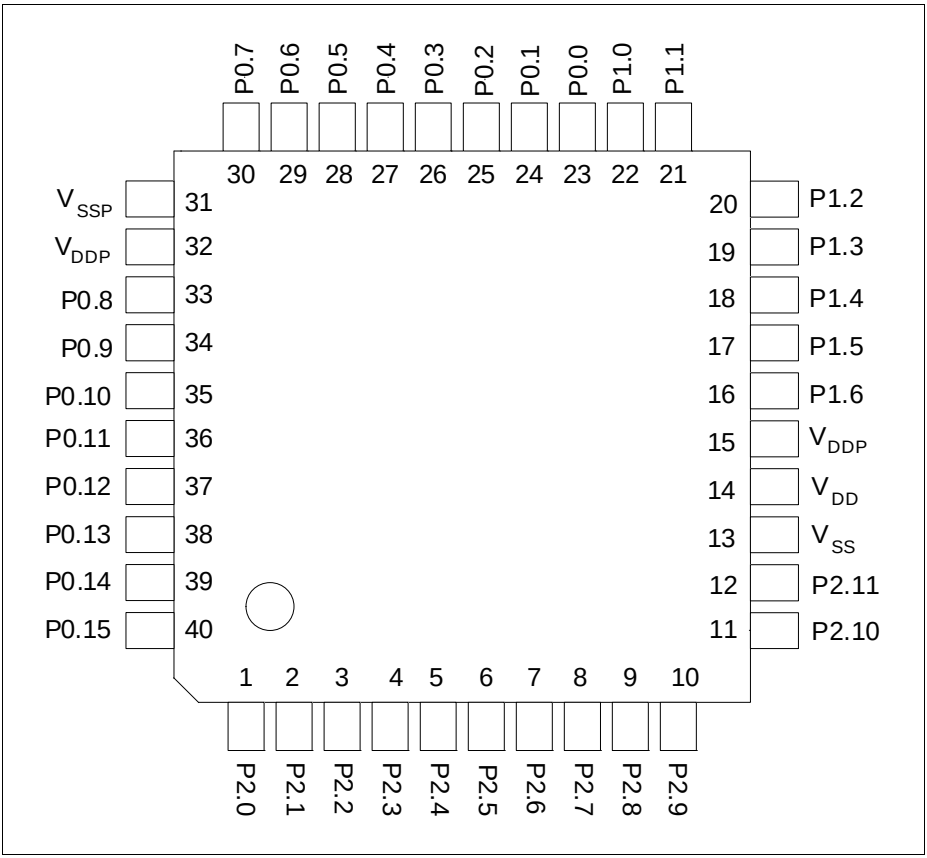

Figure 7 XMC1100 PG-VQFN-40 Pin Configuration (top view)

Table 6 Package Pin Mapping (cont'd)

Function	VQFN 40	TSSOP 38	VQFN 24	TSSOP 16	Pad Type	Notes
P0.13	38	32	22	-	STD_INOUT	
P0.14	39	33	23	13	STD_INOUT	
P0.15	40	34	24	14	STD_INOUT	
P1.0	22	16	14	-	High Current	
P1.1	21	15	13	-	High Current	
P1.2	20	14	12	-	High Current	
P1.3	19	13	11	-	High Current	
P1.4	18	12	-	-	High Current	
P1.5	17	11	-	-	High Current	
P1.6	16	-	-	-	STD_INOUT	
P2.0	1	35	1	15	STD_INOUT/ AN	
P2.1	2	36	2	-	STD_INOUT/ AN	
P2.2	3	37	3	-	STD_IN/AN	
P2.3	4	38	-	-	STD_IN/AN	
P2.4	5	1	-	-	STD_IN/AN	
P2.5	6	2	-	-	STD_IN/AN	
P2.6	7	3	4	16	STD_IN/AN	
P2.7	8	4	5	1	STD_IN/AN	
P2.8	9	5	5	1	STD_IN/AN	
P2.9	10	6	6	2	STD_IN/AN	
P2.10	11	7	7	3	STD_INOUT/ AN	
P2.11	12	8	8	4	STD_INOUT/ AN	
VSS	13	9	9	5	Power	Supply GND, ADC reference GND
VDD	14	10	10	6	Power	Supply VDD, ADC reference voltage/ ORC reference voltage

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If a pin current is outside of the **Operating Conditions** but within the overload conditions, then the parameters of this pin as stated in the Operating Conditions can no longer be guaranteed. Operation is still possible in most cases but with relaxed parameters.

Note: An overload condition on one or more pins does not require a reset.

Note: A series resistor at the pin to limit the current to the maximum permitted overload current is sufficient to handle failure situations like short to battery.

Table 12 Overload Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input current on any port pin during overload condition	I_{OV} SR	-5	–	5	mA	
Absolute sum of all input circuit currents during overload condition	I_{OVS} SR	–	–	25	mA	

Figure 9 shows the path of the input currents during overload via the ESD protection structures. The diodes against V_{DDP} and ground are a simplified representation of these ESD protection structures.

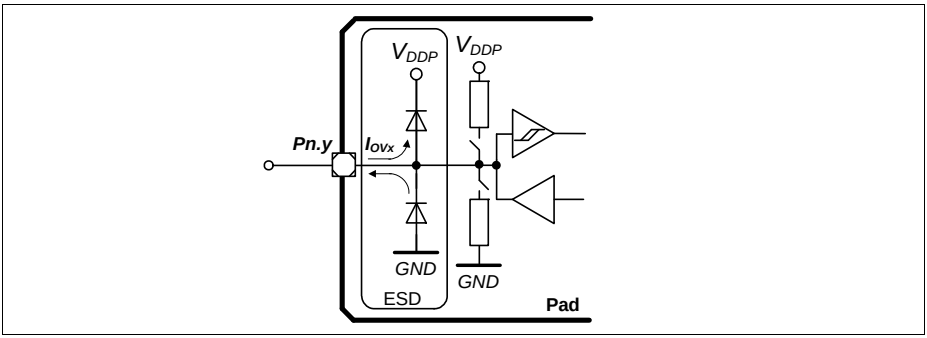

Figure 9 Input Overload Current via ESD structures

Table 13 and **Table 14** list input voltages that can be reached under overload conditions. Note that the absolute maximum input voltages as defined in the **Absolute Maximum Ratings** must not be exceeded during overload.

Table 16 Input/Output Characteristics (Operating Conditions apply) (cont'd)

Parameter	Symbol		Limit Values		Unit	Test Conditions
			Min.	Max.		
Input low voltage on port pins (Large Hysteresis)	V_{ILPL}	SR	–	0.08 × V_{DDP}	V	CMOS Mode (5 V, 3.3 V & 2.2 V)[10]
Input high voltage on port pins (Large Hysteresis)	V_{IHPL}	SR	0.85 × V_{DDP}	–	V	CMOS Mode (5 V, 3.3 V & 2.2 V)[10]
Rise time on High Current Pad[1]	t_{HCPR}	CC	–	9	ns	50 pF @ 5 V[2]
			–	12	ns	50 pF @ 3.3 V[3]
			–	25	ns	50 pF @ 1.8 V[4]
Fall time on High Current Pad[1]	t_{HCPF}	CC	–	9	ns	50 pF @ 5 V[2]
			–	12	ns	50 pF @ 3.3 V[3]
			–	25	ns	50 pF @ 1.8 V[4]
Rise time on Standard Pad[1]	t_R	CC	–	12	ns	50 pF @ 5 V[5]
			–	15	ns	50 pF @ 3.3 V[6]
			–	31	ns	50 pF @ 1.8 V[7]
Fall time on Standard Pad[1]	t_F	CC	–	12	ns	50 pF @ 5 V[5]
			–	15	ns	50 pF @ 3.3 V[6]
			–	31	ns	50 pF @ 1.8 V[7]
Input Hysteresis[8]	HYS	CC	0.08 × V_{DDP}	–	V	CMOS Mode (5 V), Standard Hysteresis
			0.03 × V_{DDP}	–	V	CMOS Mode (3.3 V), Standard Hysteresis
			0.02 × V_{DDP}	–	V	CMOS Mode (2.2 V), Standard Hysteresis
			0.5 × V_{DDP}	0.75 × V_{DDP}	V	CMOS Mode(5 V), Large Hysteresis
			0.4 × V_{DDP}	0.75 × V_{DDP}	V	CMOS Mode(3.3 V), Large Hysteresis
			0.2 × V_{DDP}	0.65 × V_{DDP}	V	CMOS Mode(2.2 V), Large Hysteresis

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Table 16 Input/Output Characteristics (Operating Conditions apply) (cont'd)

Parameter	Symbol		Limit Values		Unit	Test Conditions
			Min.	Max.		
Pin capacitance (digital inputs/outputs)	C_{IO}	CC	–	10	pF	
Pull-up resistor on port pins	R_{PUP}	CC	20	50	kohm	$V_{IN} = V_{SSP}$
Pull-down resistor on port pins	R_{PDP}	CC	20	50	kohm	$V_{IN} = V_{DDP}$
Input leakage current[9)]	I_{OZP}	CC	-1	1	µA	$0 < V_{IN} < V_{DDP}$, $T_A \leq 105$ °C
Voltage on any pin during V_{DDP} power off	V_{PO}	SR	–	0.3	V	[10)]
Maximum current per pin (excluding P1, V_{DDP} and V_{SS})	I_{MP}	SR	-10	11	mA	–
Maximum current per high currrent pins	I_{MP1A}	SR	-10	50	mA	–
Maximum current into V_{DDP} (TSSOP28/16, VQFN24)	I_{MVDD1}	SR	–	130	mA	[10)]
Maximum current into V_{DDP} (TSSOP38, VQFN40)	I_{MVDD2}	SR	–	260	mA	[10)]
Maximum current out of V_{SS} (TSSOP28/16, VQFN24)	I_{MVSS1}	SR	–	130	mA	[10)]
Maximum current out of V_{SS} (TSSOP38, VQFN40)	I_{MVSS2}	SR	–	260	mA	[10)]

1) Rise/Fall time parameters are taken with 10% - 90% of supply.
2) Additional rise/fall time valid for C_L = 50 pF - C_L = 100 pF @ 0.150 ns/pF at 5 V supply voltage.
3) Additional rise/fall time valid for C_L = 50 pF - C_L = 100 pF @ 0.205 ns/pF at 3.3 V supply voltage.
4) Additional rise/fall time valid for C_L = 50 pF - C_L = 100 pF @ 0.445 ns/pF at 1.8 V supply voltage.
5) Additional rise/fall time valid for C_L = 50 pF - C_L = 100 pF @ 0.225 ns/pF at 5 V supply voltage.
6) Additional rise/fall time valid for C_L = 50 pF - C_L = 100 pF @ 0.288 ns/pF at 3.3 V supply voltage.
7) Additional rise/fall time valid for C_L = 50 pF - C_L = 100 pF @ 0.588 ns/pF at 1.8 V supply voltage.

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Table 17 ADC Characteristics (Operating Conditions apply)[1] (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum sample rate in 8-bit mode [3]	f_{C8} CC	–	–	f_{ADC} / 38.5	–	1 sample pending
		–	–	f_{ADC} / 54.5	–	2 samples pending
RMS noise [4]	EN_{RMS} CC	–	1.5	–	LSB 12	DC input, V_{DD} = 5.0 V, V_{AIN} = 2.5 V, 25°C
DNL error	EA_{DNL} CC	–	±2.0	–	LSB 12	
INL error	EA_{INL} CC	–	±4.0	–	LSB 12	
Gain error with external reference	EA_{GAIN} CC	–	±0.5	–	%	SHSCFG.AREF = 00_B (calibrated)
Gain error with internal reference [5]	EA_{GAIN} CC	–	±3.6	–	%	SHSCFG.AREF = $1X_B$ (calibrated), -40°C - 105°C
		–	±2.0	–	%	SHSCFG.AREF = $1X_B$ (calibrated), 0°C - 85°C
Offset error	EA_{OFF} CC	–	±8.0	–	mV	Calibrated, V_{DD} = 5.0 V

1) The parameters are defined for ADC clock frequency f_{SH} = 32MHz.

2) No pending samples assumed, excluding sampling time and calibration.

3) Includes synchronization and calibration (average of gain and offset calibration).

4) This parameter can also be defined as an SNR value: SNR[dB] = 20 × log(A_{MAXeff} / N_{RMS}).
With $A_{MAXeff} = 2^N / 2$, SNR[dB] = 20 × log (2048 / N_{RMS}) [N = 12].
N_{RMS} = 1.5 LSB12, therefore, equals SNR = 20 × log (2048 / 1.5) = 62.7 dB.

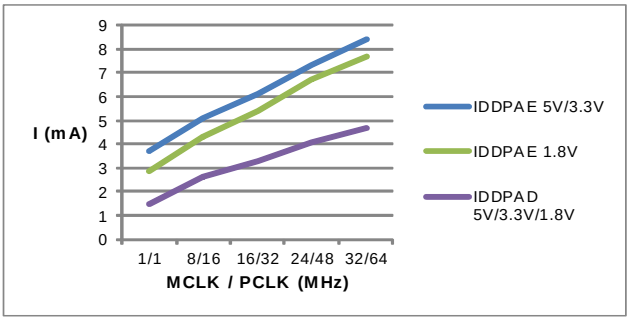
5) Includes error from the reference voltage.

Table 19 Power Supply Parameters; V_{DDP} = 5V

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.[1]	Max.		
Sleep mode current Peripherals clock disabled Flash active f_{MCLK} / f_{PCLK} in MHz[5]	I_{DDPSD} CC	–	1.8	–	mA	32 / 64
			1.7	–	mA	24 / 48
			1.6	–	mA	16 / 32
			1.5	–	mA	8 / 16
			1.4	–	mA	1 / 1
Sleep mode current Peripherals clock disabled Flash powered down f_{MCLK} / f_{PCLK} in MHz[6]	I_{DDPSR} CC	–	1.2	–	mA	32 / 64
			1.1	–	mA	24 / 48
			1.0	–	mA	16 / 32
			0.8	–	mA	8 / 16
			0.7	–	mA	1 / 1
Deep Sleep mode current[7]	I_{DDPDS} CC	–	0.24	–	mA	
Wake-up time from Sleep to Active mode[8]	t_{SSA} CC	–	6	–	cycles	
Wake-up time from Deep Sleep to Active mode[9]	t_{DSA} CC	–	280	–	µsec	

1) The typical values are measured at T_A = + 25 °C and V_{DDP} = 5 V.
2) CPU and all peripherals clock enabled, Flash is in active mode.
3) CPU enabled, all peripherals clock disabled, Flash is in active mode.
4) CPU in sleep, all peripherals clock enabled and Flash is in active mode.
5) CPU in sleep, Flash is in active mode.
6) CPU in sleep, Flash is powered down and code executed from RAM after wake-up.
7) CPU in sleep, peripherals clock disabled, Flash is powered down and code executed from RAM after wake-up.
8) CPU in sleep, Flash is in active mode during sleep mode.
9) CPU in sleep, Flash is in powered down mode during deep sleep mode.

Figure 11 shows typical graphs for active mode supply current for V_{DDP} = 5V, V_{DDP} = 3.3V, V_{DDP} = 1.8V across different clock frequencies.



Condition:
1. TA = +25° C

Figure 11 Active mode, a) peripherals clocks enabled, b) peripherals clocks disabled: Supply current I_{DDPA} over supply voltage V_{DDP} for different clock frequencies

Figure 12 shows typical graphs for sleep mode current for V_{DDP} = 5V, V_{DDP} = 3.3V, V_{DDP} = 1.8V across different clock frequencies.

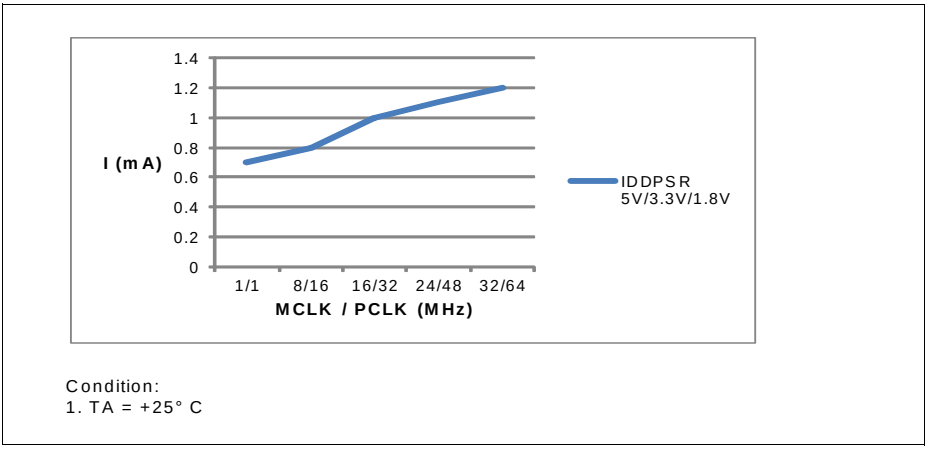


Figure 12 Sleep mode, peripherals clocks disabled, Flash powered down: Supply current I_{DDPSR} over supply voltage V_{DDP} for different clock frequencies

3.3.3 On-Chip Oscillator Characteristics

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 23 provides the characteristics of the 64 MHz clock output from the digital controlled oscillator, DCO1 in XMC1100.

Table 23 64 MHz DCO1 Characteristics (Operating Conditions apply)

Parameter	Symbol		Limit Values			Unit	Test Conditions
			Min.	Typ.	Max.		
Nominal frequency	f_{NOM}	CC	–	64	–	MHz	under nominal conditions[1] after trimming
Accuracy[2]	Δf_{LT}	CC	-1.7	–	3.4	%	with respect to f_{NOM}(typ), over temperature (0 °C to 85 °C)
			-3.9	–	4.0	%	with respect to f_{NOM}(typ), over temperature (-40 °C to 105 °C)

1) The deviation is relative to the factory trimmed frequency at nominal V_{DDC} and T_A = + 25 °C.

2) The accuracy of the DCO1 oscillator can be further improved through alternative methods, refer to XMC1000 Oscillator Handling Application Note.

3.3.4 Serial Wire Debug Port (SW-DP) Timing

The following parameters are applicable for communication through the SW-DP interface.

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 25 SWD Interface Timing Parameters(Operating Conditions apply)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
SWDCLK high time	t_1 SR	50	–	500000	ns	–
SWDCLK low time	t_2 SR	50	–	500000	ns	–
SWDIO input setup to SWDCLK rising edge	t_3 SR	10	–	–	ns	–
SWDIO input hold after SWDCLK rising edge	t_4 SR	10	–	–	ns	–
SWDIO output valid time after SWDCLK rising edge	t_5 CC	–	–	68	ns	C_L = 50 pF
		–	–	62	ns	C_L = 30 pF
SWDIO output hold time from SWDCLK rising edge	t_6 CC	4	–	–	ns	

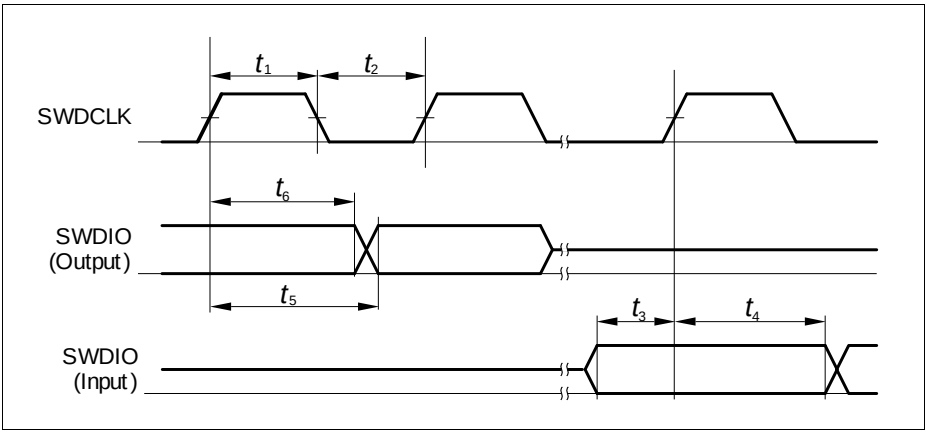


Figure 18 SWD Timing

3.3.6 Peripheral Timings

Note: These parameters are not subject to production test, but verified by design and/or characterization.

3.3.6.1 Synchronous Serial Interface (USIC SSC) Timing

The following parameters are applicable for a USIC channel operated in SSC mode.

Note: Operating Conditions apply.

Table 27 USIC SSC Master Mode Timing

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
SCLKOUT master clock period	t_{CLK}	CC	62.5	–	–	ns	
Slave select output SELO active to first SCLKOUT transmit edge	t_1	CC	80	–	–	ns	
Slave select output SELO inactive after last SCLKOUT receive edge	t_2	CC	0	–	–	ns	
Data output DOUT[3:0] valid time	t_3	CC	-10	–	10	ns	
Receive data input DX0/DX[5:3] setup time to SCLKOUT receive edge	t_4	SR	80	–	–	ns	
Data input DX0/DX[5:3] hold time from SCLKOUT receive edge	t_5	SR	0	–	–	ns	

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Table 28 USIC SSC Slave Mode Timing

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
DX1 slave clock period	t_{CLK}	SR	125	–	–	ns	
Select input DX2 setup to first clock input DX1 transmit edge[1]	t_{10}	SR	10	–	–	ns	
Select input DX2 hold after last clock input DX1 receive edge[1]	t_{11}	SR	10	–	–	ns	
Receive data input DX0/DX[5:3] setup time to shift clock receive edge[1]	t_{12}	SR	10	–	–	ns	
Data input DX0/DX[5:3] hold time from clock input DX1 receive edge[1]	t_{13}	SR	10	–	–	ns	
Data output DOUT[3:0] valid time	t_{14}	CC	-	–	80	ns	

1) These input timings are valid for asynchronous input signal handling of slave select input, shift clock input, and receive data input (bits DXnCR.DSEN = 0).

3.3.6.2 Inter-IC (IIC) Interface Timing

The following parameters are applicable for a USIC channel operated in IIC mode.

Note: Operating Conditions apply.

Table 29 USIC IIC Standard Mode Timing[1)]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Fall time of both SDA and SCL	t_1 CC/SR	-	-	300	ns	
Rise time of both SDA and SCL	t_2 CC/SR	-	-	1000	ns	
Data hold time	t_3 CC/SR	0	-	-	µs	
Data set-up time	t_4 CC/SR	250	-	-	ns	
LOW period of SCL clock	t_5 CC/SR	4.7	-	-	µs	
HIGH period of SCL clock	t_6 CC/SR	4.0	-	-	µs	
Hold time for (repeated) START condition	t_7 CC/SR	4.0	-	-	µs	
Set-up time for repeated START condition	t_8 CC/SR	4.7	-	-	µs	
Set-up time for STOP condition	t_9 CC/SR	4.0	-	-	µs	
Bus free time between a STOP and START condition	t_{10} CC/SR	4.7	-	-	µs	
Capacitive load for each bus line	C_b SR	-	-	400	pF	

1) Due to the wired-AND configuration of an IIC bus system, the port drivers of the SCL and SDA signal lines need to operate in open-drain mode. The high level on these lines must be held by an external pull-up device, approximalely 10 kOhm for operation at 100 kbit/s, approximately 2 kOhm for operation at 400 kbit/s.

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4 Package and Reliability

The XMC1100 is a member of the XMC™1000 Family of microcontrollers. It is also compatible to a certain extent with members of similar families or subfamilies.

Each package is optimized for the device it houses. Therefore, there may be slight differences between packages of the same pin-count but for different device types. In particular, the size of the exposed die pad may vary.

If different device types are considered or planned for an application, it must be ensured that the board layout fits all packages under consideration.

4.1 Package Parameters

Table 33 provides the thermal characteristics of the packages used in XMC1100.

Table 33 Thermal Characteristics of the Packages

Parameter	Symbol	Limit Values		Unit	Package Types
		Min.	Max.		
Exposed Die Pad Dimensions	Ex × Ey CC	-	2.7 × 2.7	mm	PG-VQFN-24-19
		-	3.7 × 3.7	mm	PG-VQFN-40-13
Thermal resistance Junction-Ambient	$R_{\Theta JA}$ CC	-	104.6	K/W	PG-TSSOP-16-8[1)]
		-	70.3	K/W	PG-TSSOP-38-9[1)]
		-	46.0	K/W	PG-VQFN-24-19[1)]
		-	38.4	K/W	PG-VQFN-40-13[1)]

1) Device mounted on a 4-layer JEDEC board (JESD 51-5); exposed pad soldered.

Note: For electrical reasons, it is required to connect the exposed pad to the board ground V_{SSP}, independent of EMC and thermal requirements.

4.1.1 Thermal Considerations

When operating the XMC1100 in a system, the total heat generated in the chip must be dissipated to the ambient environment to prevent overheating and the resulting thermal damage.

The maximum heat that can be dissipated depends on the package and its integration into the target board. The “Thermal resistance $R_{\Theta JA}$” quantifies these parameters. The power dissipation must be limited so that the average junction temperature does not exceed 115 °C.

The difference between junction temperature and ambient temperature is determined by $\Delta T = (P_{INT} + P_{IOSTAT} + P_{IODYN}) \times R_{\Theta JA}$

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4.2 Package Outlines

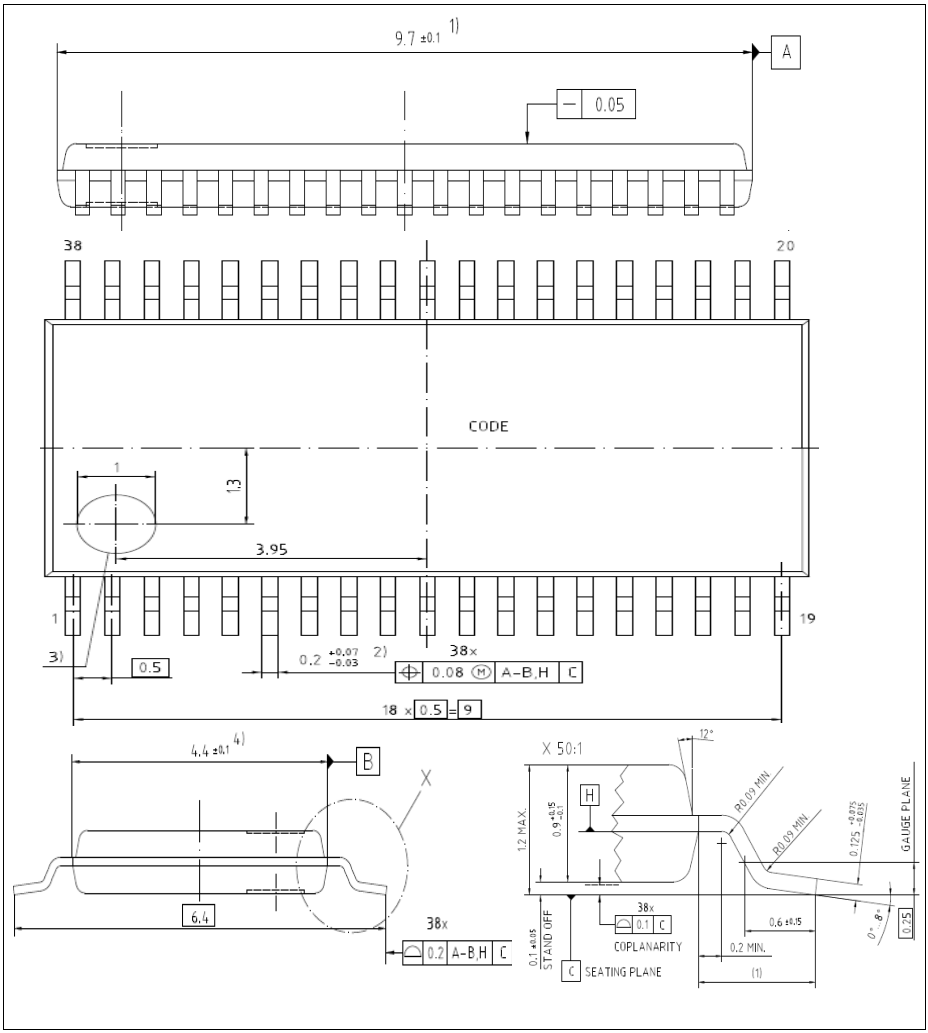

Figure 23 PG-TSSOP-38-9

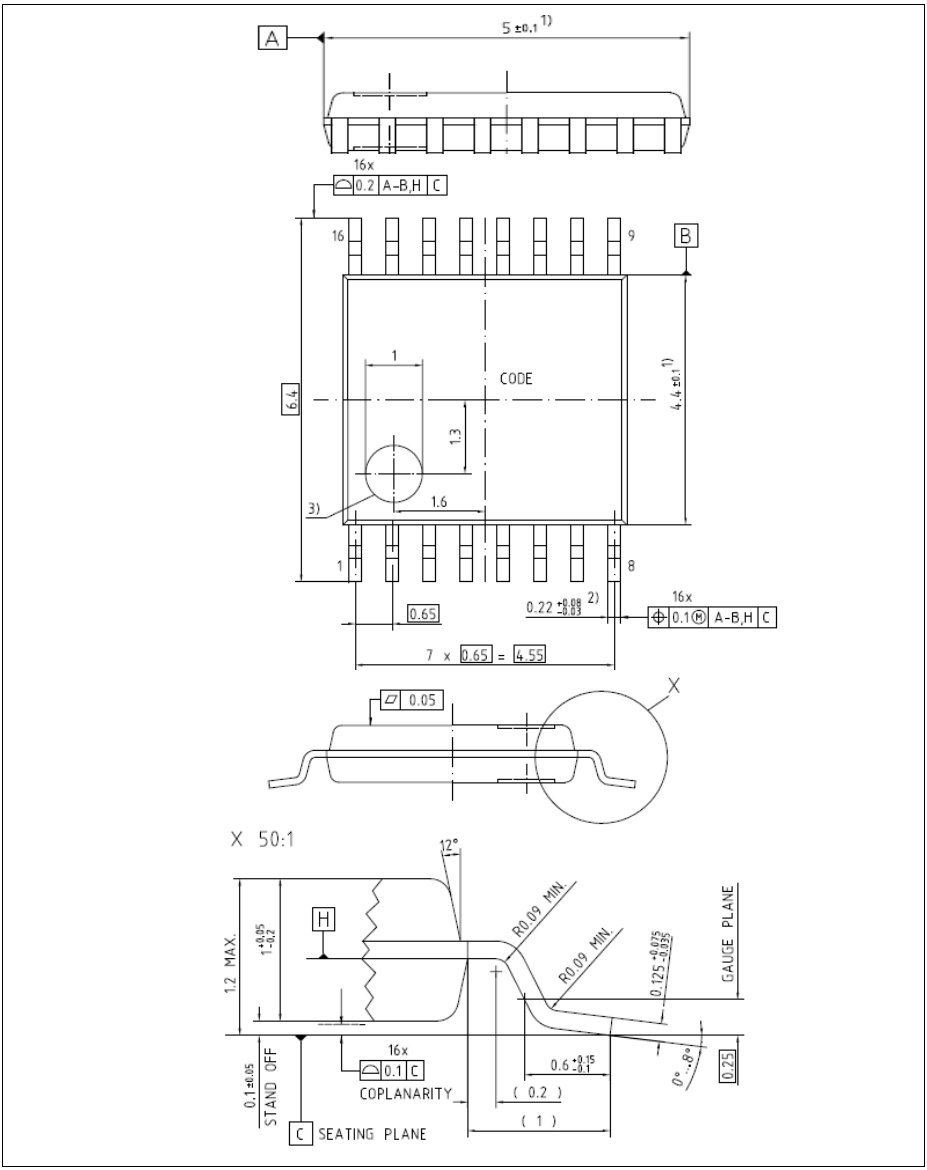

Figure 24 PG-TSSOP-16-8

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